PEMH16; PUMH16

NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω Rev. 04 — 15 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN Resistor-Equipped Transistors (RET).

Table 1. Product overview

Type number	Package		NPN/PNP	PNP/PNP
	NXP	JEITA	complement	complement
PEMH16	SOT666	-	PEMD16	PEMB16
PUMH16	SOT363	SC-88	PUMD16	PUMB16

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data Symbol Conditions Unit Parameter Min Тур Max VCEO open base 50 V collector-emitter voltage --100 I_{O} output current mΑ -R1 bias resistor 1 (input) kΩ 15.4 22 28.6 R2/R1 bias resistor ratio 1.7 2.1 2.6



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NPN/NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

2. Pinning information

Pinning		
Description	Simplified outline	Symbol
GND (emitter) TR1		
input (base) TR1	6 5 4	
output (collector) TR2		
GND (emitter) TR2		
input (base) TR2		
output (collector) TR1	001aab555	
	Description GND (emitter) TR1 input (base) TR1 output (collector) TR2 GND (emitter) TR2 input (base) TR2 input (base) TR2	DescriptionSimplified outlineGND (emitter) TR1input (base) TR1output (collector) TR2GND (emitter) TR2input (base) TR2

3. Ordering information

Table 4. Ordering information					
Type number	Package				
	Name	Description	Version		
PEMH16	-	plastic surface mounted package; 6 leads	SOT666		
PUMH16	SC-88	plastic surface mounted package; 6 leads	SOT363		

4. Marking

Table 5.Marking codes

Type number	Marking code ^[1]	
PEMH16	5K	
PUMH16	H3*	

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	7	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-7	V
I _O	output current		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1][2] _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	300	mW
	SOT666		<u>[1][2]</u>	300	mW

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	sistor						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	SOT363		<u>[1]</u>	-	-	625	K/W
	SOT666		[1][2]	-	-	625	K/W
Per devic	ce						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	SOT363		<u>[1]</u>	-	-	416	K/W
	SOT666		[1][2]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

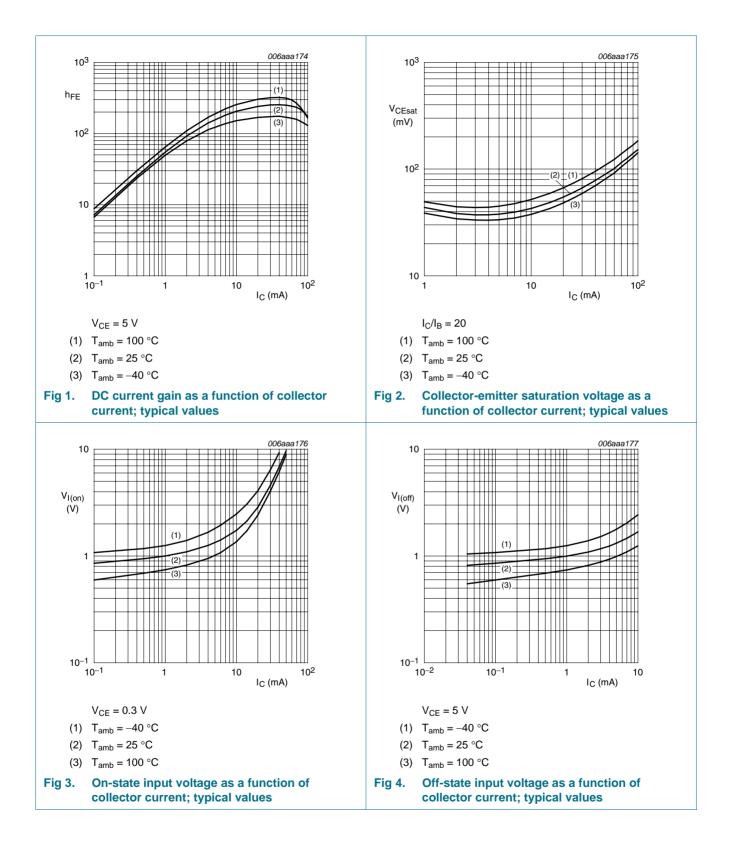
Table 8. Characteristics

 $T_{amb} = 25 \ ^{\circ}C$ unless otherwise specified.

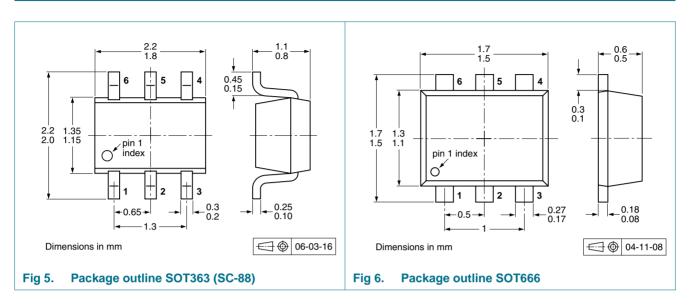
unio						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$\label{eq:VCE} \begin{array}{l} V_{CE} = 30 \; V; \; I_{B} = 0 \; A; \\ T_{j} = 150 \; ^{\circ}C \end{array}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	120	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C}$ = 10 mA; $I_{\rm B}$ = 0.5 mA	-	-	150	mV
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_{C} = 100 μ A	-	0.8	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}$	2	1.1	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz} \end{array}$	-	-	2.5	pF

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8. Package outline



9. Packing information

Table 9.Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity			
				3000	4000	8000	10000
PEMH16 SOT666		2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMH16	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

[1] For further information and the availability of packing methods, see <u>Section 12</u>.

[2] T1: normal taping

[3] T2: reverse taping

10. Revision history

Table 10. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH16_PUMH16_4	20091115	Product data sheet	-	PEMH16_PUMH16_3
Modifications:	including ner content.	eet was changed to reflect t w legal definitions and discla ckage outline SOT363 (SC-	aimers. No changes w	
PEMH16_PUMH16_3	20050607	Product data sheet	-	PUMH16_2
PUMH16_2	20040414	Product specification	-	PUMH16_1
PUMH16_1	20031009	Product specification	-	-

PEMH16_PUMH16_4

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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